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Docket No.: 0002802.00169US1 (PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Martin W. Rupich et al.

Confirmation No.:

3570

Application No.:

10/812,676

Art Unit:

1722

Filed:

March 30, 2004

Examiner:

R. M. Kunemund

Title:

DEPOSITION OF BUFFER LAYERS ON TEXTURED METAL

SURFACES

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT (IDS)

Dear Sir:

This Information Disclosure Statement is being filed simultaneously with a Request for Continued Examination. No fee is believed to be due.

Applicants request that the Examiner initial and return a copy of the enclosed Form PTO SB-08 with the next communication.

Respectfully submitted,

Dated: December 28, 2006

Registration No.: 36,268 Attorney for Applicant(s)

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PTO/SB/08A/B (09-06) Approved for use through 03/31/2007. OMB 0651-0031
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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

2 Sheet 1

Complete if Known			
Application Number	10/812,676-Conf. #3570		
Filing Date	March 30, 2004		
First Named Inventor	Martin W. Rupich		
Art Unit	1722		
Examiner Name	R. M. Kunemund		
Attorney Docket Number	0002802.00169US1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-08/943,047	10-01-1997	Thieme	
	AB	US-09/007,373	01-15-1998	Fritzemeier et al.	
	AC	US-60/447,613	06-10-2003	Rupich et al	
	AD*	US-2002/0056401-A1	05-16-2002	Rupich et al	
	AE*	US-2002/0178999-A1	12-05-2002	Beach et al.	
	AF*	US-2002/0056401-A1	05-16-2002	Rupich et al.	
	AG*	US-2003/0130129-A1	07-10-2003	Seleznev et al	
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	AI*	US-2005/0159298-A1	07-21-2005	Rupich, et al	
	AJ*	US-5,231,074	07-27-1993	Cima et al.	
	AK*	US-5,340,794	08-23-1994	Tallon et al.	
	AL*	US-6,022,832	02-08-2000	Fritzemeier et al.	
	AM*	US-6,190,752	02-20-2001	Do et al.	
	AN*	US-6,202,287	03-20-2001	Otto	
	AO*	US-6,399,154	06-04-2002	Williams et al	
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	AS*	US-6,602,588	08-05-2003	Kwon et al.	
	AT*	US-6,624,122-B1	09-23-2003	Holesinger et al.	
	AU*	US-6,669,774	12-30-2003	Zhang et al	
	AV*	US-6,673,387	01-06-2004	Zhang et al	
	AW*	US-6,730,410	05-04-2004	Fritzemeier et al	
	AX*	US-6,745,059-A1	06-01-2004	Buczek et al	
	AY*	US-6,797,313	09-28-2004	Fritzemeier et al	
	AZ*	US-6,828,507	12-07-2004	Fritzemeier et al	
	AA1*	US-6,974,501-B1	12-13-2005	Zhang et al	

	FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
	ВА	WO-98/58415	12-23-1998	Massachusetts Institute of Technology			
	ВВ	WO-99/25908	05-27-1999	The Board of Trustees of the Leland Stanford Junior University			
	вс	WO-01/08236	02-01-2001	American Superconductor Corporation			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. *CITE NO.: Those application(s) which are marked with an single asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. 'Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Examiner	Date
Signature	Considered

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Substitute for form 1449/PTO				Complete if Known		
"	000000 101 101111 144077 1 0			Application Number	10/812,676-Conf. #3570	
	NFORMATION	l DI	SCLOSURE	Filing Date	March 30, 2004	
l s	STATEMENT BY APPLICANT			First Named Inventor	Martin W. Rupich	
				Art Unit	1722	
	(Use as many sheets as necessary)			Examiner Name	R. M. Kunemund	
Sheet	2	of	2	Attorney Docket Number	0002802.00169US1	

		NON PATENT LITERATURE DOCUMENTS			
Examiner Cite Initials No.1					
	CA	EUROPEAN PATENT OFFICE, International Search Report of PCT/US2005/010593 mailed 14 November 2005, 3 pages			
	СВ	PARANTHAMAN, M. et al, "Growth of Textured Buffer Layers and Superconductors on Rolled Ni Substrates Using Sol-gel Alkoxide Precursors", Ninth CIMTEC World Ceramics Contress and Forum on New Materials, Florence, Italy, 1998, pp. 185-192			
	СС	PARANTHAMAN, S. et al, "Epitaxial Growth of BaZrO ₃ Films on Single Crystal Oxide Substrates Using Sol-Gel Alkoxide Precursors", Mater. Res. Bull., Vol. 32, No. 12, 1997, pp. 1697-1704			
	CD	SATHYAMURTHY et al, "Application of Metal-Organic Decomposition Techniques for the Deposition of Buffer Layers and Y123 for Coated-Conductor Fabrication", Physica C (Netherlands), 2000, Vol. 329, pp. 58-68			
	CE	SATHYAMURTHY et al, "Chemical Solution Deposition of Highly Oriented Strontium Titanate Buffer Layers for Coated Conductors", Supercond. Sci. Technol., 2000, Vol. 13, pp. L1-L3			
	CF	SCHWARTZ, "Control of Microstructure and Orientation in Solution-Deposited BaTiO ₃ and Sr TiO ₃ Thin Films", J. Am. Ceram. Soc., 1999, Vol. 82, No. 9, pp. 2359-2367			
	CG	SHOUP et al, "Sol-Gel Synthesis of LaA10 ₃ ; Epitaxial Growth of LaA10 ₃ Thin Films on SrTiO ₃ (100)", J. Mat. Research, 1997, Vol. 12, pp. 1017-21			

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Examiner	Date
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¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.